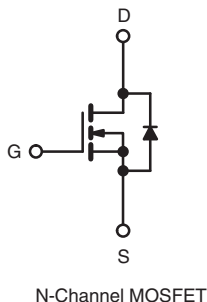
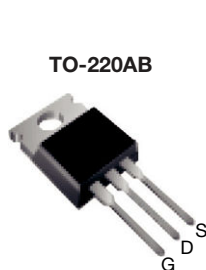


## D Series Power MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	650	
$R_{DS(on)}$ max. at 25 °C ( $\Omega$ )	$V_{GS} = 10$ V	0.340
$Q_g$ (Max.) (nC)	90	
$Q_{gs}$ (nC)	14	
$Q_{gd}$ (nC)	22	
Configuration	Single	



### FEATURES

- Optimal Design
  - Low Area Specific On-Resistance
  - Low Input Capacitance ( $C_{iss}$ )
  - Reduced Capacitive Switching Losses
  - High Body Diode Ruggedness
  - Avalanche Energy Rated (UIS)
- Optimal Efficiency and Operation
  - Low Cost
  - Simple Gate Drive Circuitry
  - Low Figure-of-Merit (FOM):  $R_{on} \times Q_g$
  - Fast Switching
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- Consumer Electronics
  - Displays (LCD or Plasma TV)
- Lighting
- Industrial
  - Welding
  - Induction Heating
  - Motor Drives
  - Battery Chargers
- SMPS

### ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	SiHP17N60D-E3
Lead (Pb)-free and Halogen-free	SiHP17N60D-GE3

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	600	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	
Continuous Drain Current ( $T_J = 150$ °C)	$V_{GS}$ at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	48	
Linear Derating Factor		2.22	W/°C
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	165.6	mJ
Maximum Power Dissipation	$P_D$	277.8	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to + 150	°C
Drain-Source Voltage Slope	$dV/dt$	24	V/ns
Reverse Diode $dV/dt$ <sup>d</sup>		0.2	
Soldering Recommendations (Peak Temperature) <sup>c</sup>	for 10 s	300	°C


#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 2.3$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 12$  A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$ , starting  $T_J = 25$  °C.

**THERMAL RESISTANCE RATINGS**

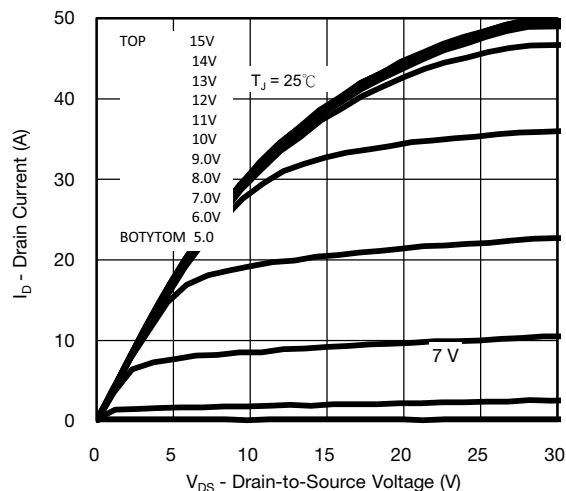
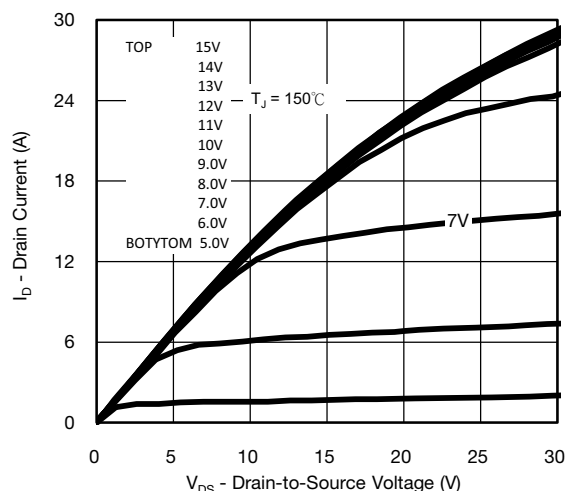
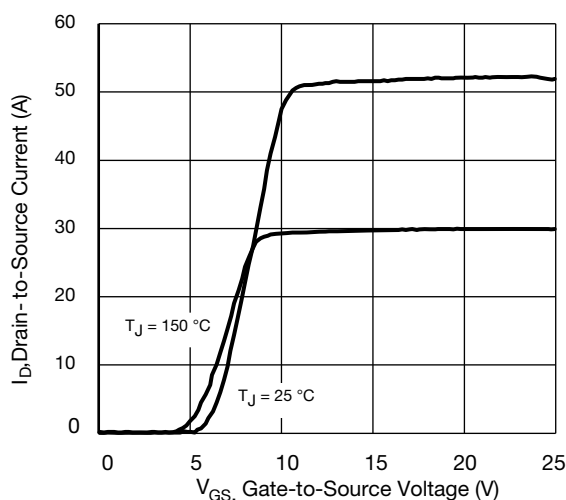
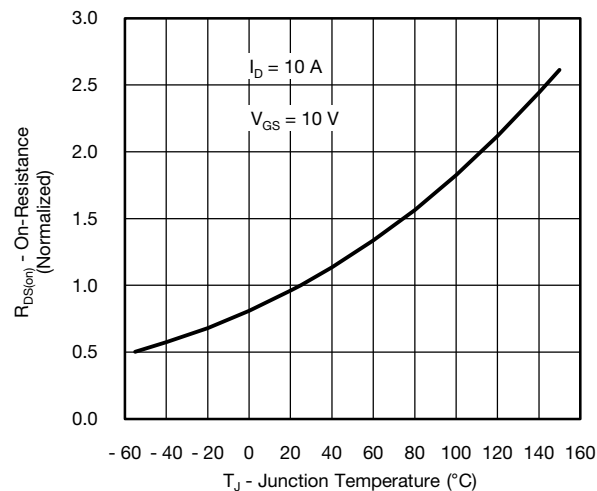
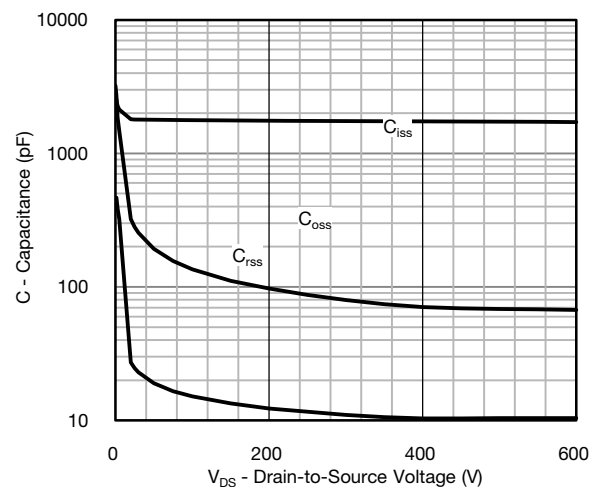
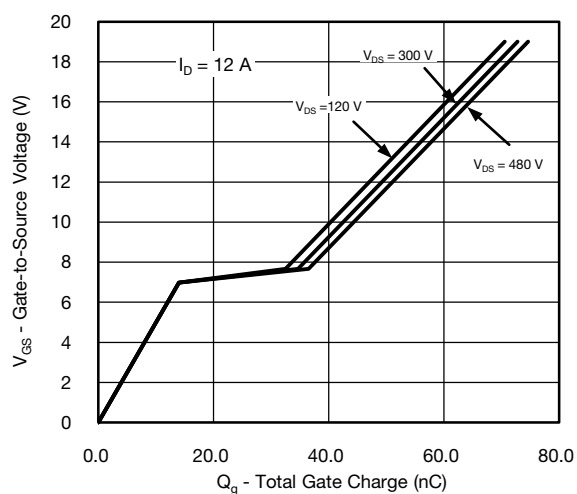
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.45	

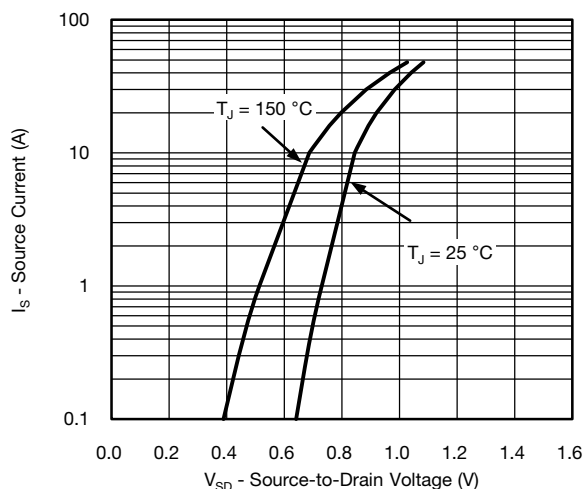
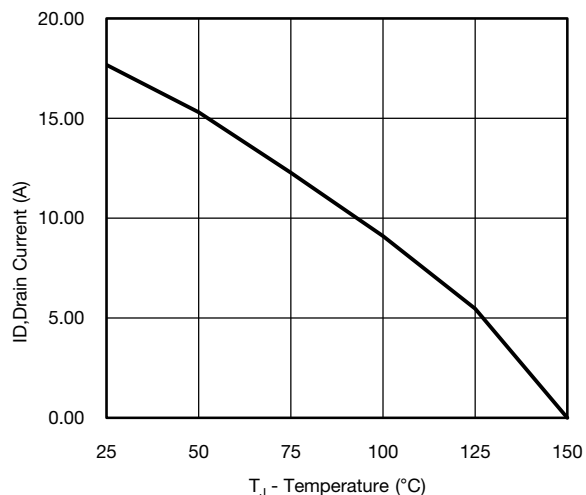
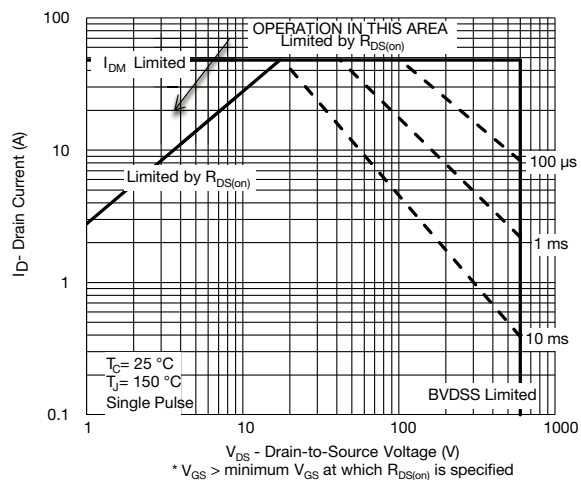
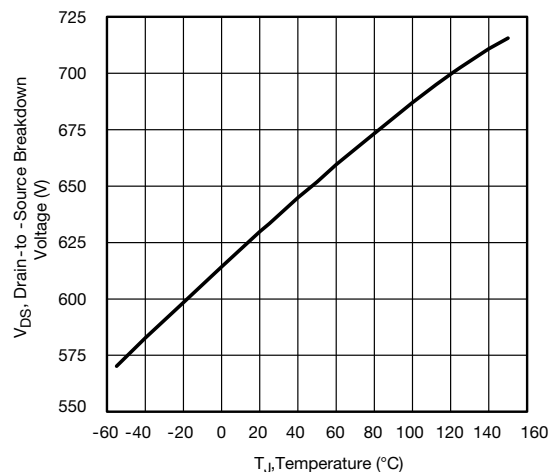
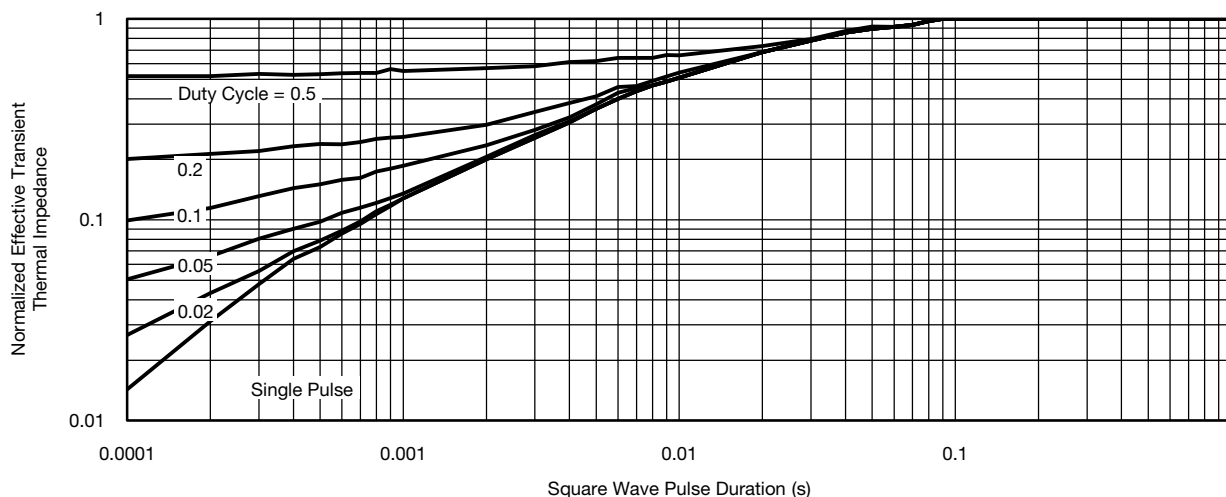
**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

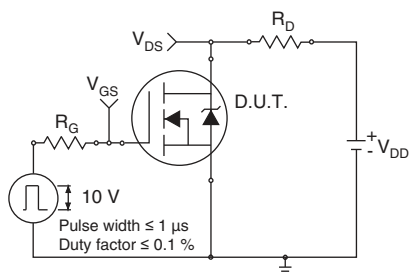
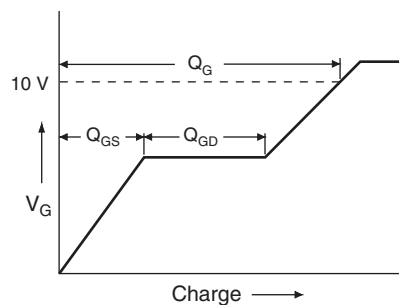
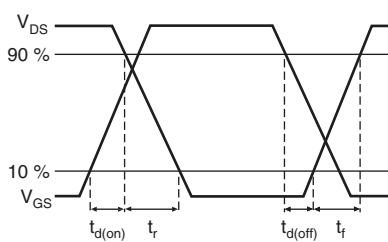
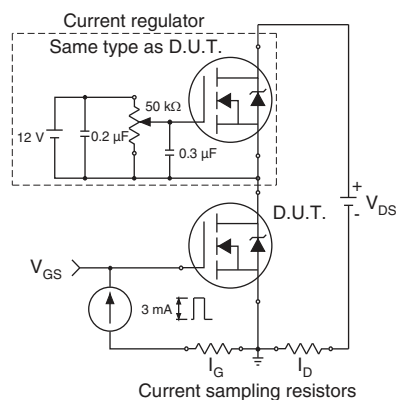
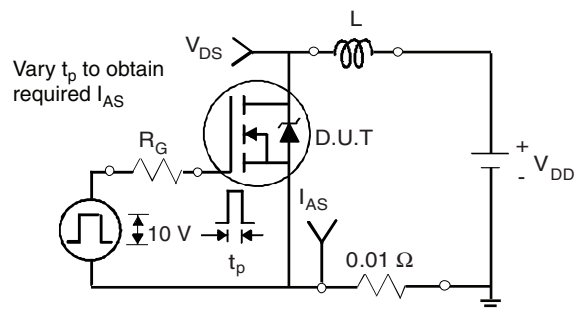
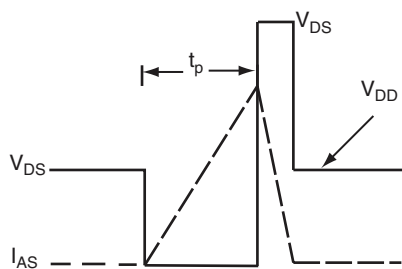
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	600	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^{\circ}\text{C}$ , $I_D = 1\text{ mA}$	-	0.7	-	V/ $^{\circ}\text{C}$
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3	-	5	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30\text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 600\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 480\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^{\circ}\text{C}$	-	-	100	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 8\text{ A}$	-	0.275	0.340	$\Omega$
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 50\text{ V}$ , $I_D = 8\text{ A}$	-	6.2	-	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$	-	1780	-	pF
Output Capacitance	$C_{oss}$		-	140	-	
Reverse Transfer Capacitance	$C_{rss}$		-	15	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$ , $I_D = 8\text{ A}$ , $V_{DS} = 480\text{ V}$	-	45	90	nC
Gate-Source Charge	$Q_{gs}$		-	14	-	
Gate-Drain Charge	$Q_{gd}$		-	22	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300\text{ V}$ , $I_D = 8\text{ A}$ $R_g = 9.1\text{ }\Omega$ , $V_{GS} = 10\text{ V}$	-	22	45	ns
Rise Time	$t_r$		-	56	85	
Turn-Off Delay Time	$t_{d(off)}$		-	37	75	
Fall Time	$t_f$		-	30	60	
Internal Gate Resistance	$R_g$	$f = 1\text{ MHz}$ , open drain	-	1.6	-	$\Omega$
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	17	A
Pulsed Diode Forward Current	$I_{SM}$		-	-	48	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^{\circ}\text{C}$ , $I_S = 8\text{ A}$ , $V_{GS} = 0\text{ V}$	-	-	1.5	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^{\circ}\text{C}$ , $I_F = I_S$ , $dI/dt = 100\text{ A}/\mu\text{s}$ , $V_R = 20\text{ V}$	-	633	950	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	7	15	$\mu\text{C}$
Reverse Recovery Current	$I_{RRM}$		-	21	42	A

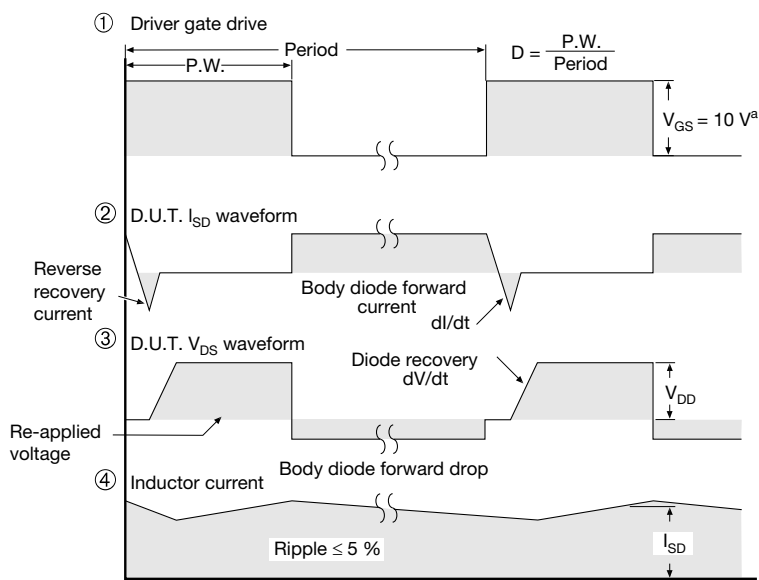
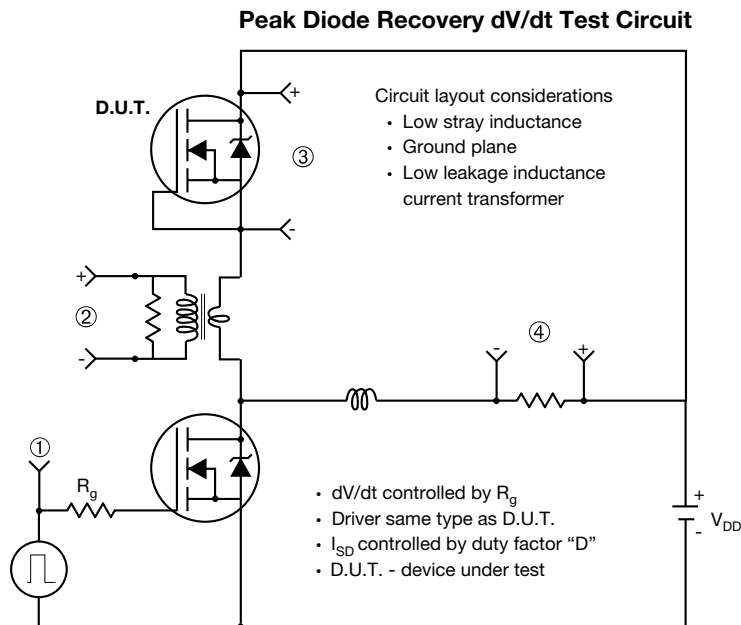
**Note**

a. Repetitive rating; pulse width limited by maximum junction temperature.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics,  $T_C = 150^\circ\text{C}$** 

**Fig. 2 - Typical Output Characteristics,  $T_C = 150^\circ\text{C}$** 

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**


**Fig. 7 - Typical Source-Drain Diode Forward Voltage**

**Fig. 9 - Maximum Drain Current vs. Case Temperature**

**Fig. 8 - Maximum Safe Operating Area**

**Fig. 10 - Typical Drain-to-Source Voltage vs. Temperature**

**Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case**


**Fig. 12 - Switching Time Test Circuit**

**Fig. 16 - Basic Gate Charge Waveform**

**Fig. 13 - Switching Time Waveforms**

**Fig. 17 - Gate Charge Test Circuit**

**Fig. 14 - Unclamped Inductive Test Circuit**

**Fig. 15 - Unclamped Inductive Waveforms**



**Fig. 18 - For N-Channel**

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